N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

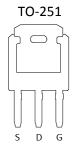
Typical	Дþ	plica	atior	ıs:
.,	, .P		~	

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V _{DS} (V)	I⊳(A)			
100	7 @ V _{GS} = 10V	60 ^a		
100	9 @ V _{GS} = 4.5V	00		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			100	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current ^a T _c =25°C			60	Α		
Pulsed Drain Current ^b	I _{DM}	240	Α			
Continuous Source Current (Diode Conduction) ^a	I _S	60	Α			
Power Dissipation ^a	P_{D}	50	W			
Operating Junction and Storage Temperature Range			-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

1

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

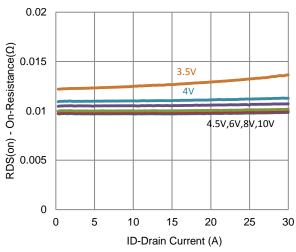
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	1 10		uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			uA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			7	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			9	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		11		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		0.83		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		51		nC	
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		22			
Gate-Drain Charge	Q_gd	1D = 20 A		15			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 50 \text{ V}, R_1 = 2.5 \Omega,$		20			
Rise Time	t _r	$V_{DS} = 50 \text{ V}, N_L - 2.5 \Omega,$ $I_D = 20 \text{ A},$		16		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		152			
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.22		42			
Input Capacitance	C _{iss}			7442			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		376		pF	
Reverse Transfer Capacitance	C_{rss}			176			

Notes

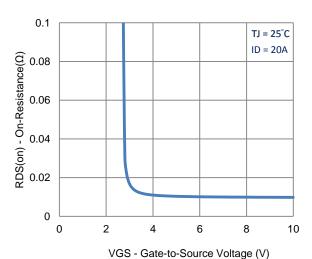
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

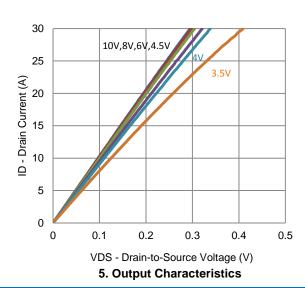
Typical Electrical Characteristics



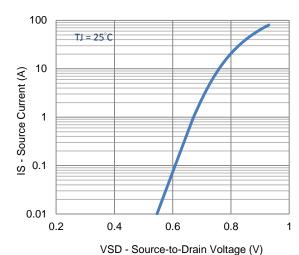
1. On-Resistance vs. Drain Current



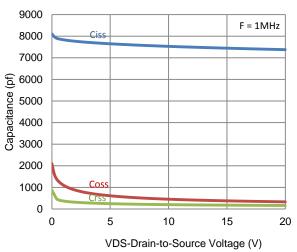
3. On-Resistance vs. Gate-to-Source Voltage



2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



6. Capacitance

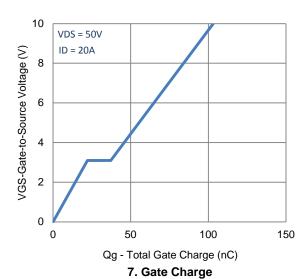
Typical Electrical Characteristics

2.5

2

1.5

 $RDS(on) - On-Resistance(\Omega) \\ (Normalized)$

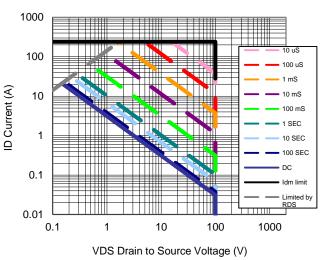


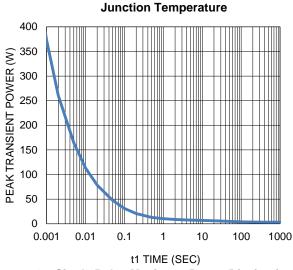
0.5 -50 -25 0 25 50 75 100 125

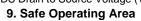
TJ -JunctionTemperature(°C)

8. Normalized On-Resistance Vs

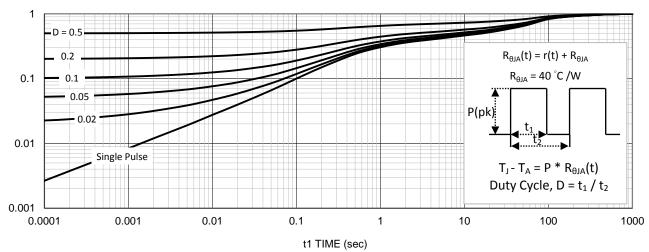
150





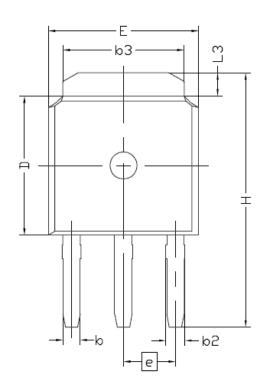


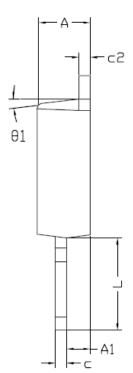
10. Single Pulse Maximum Power Dissipation

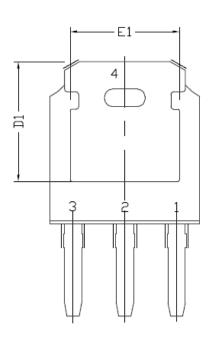


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVMDDI	DIMENS	[DNAL F	REQMTS	INCH	ES REG	2TM
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX
E	6.35	6.60	6.73	0.250	0,260	0.265
L	3.70	4.05	4,40	0.146	0.159	0,173
L3	0.89	1.016	1.27	0.035	0.040	0.050
D	6.00	6,10	6.20	0,236	0.240	0.244
Н	10.80	11.15	11.50	0.425	0,439	0.453
b	0,635	0.76	0.889	0.025	0.030	0.035
b2	0.762	0.84	1.143	0.030	0.033	0.045
b3	5.21	5,34	5,46	0,205	0,210	0,215
6	2.286 BSC			0.090 BSC		
Α	2.20	2,30	2,38	0.087	0.091	0.094
A1	0.94	1.04	1.14	0.037	0.041	0.045
C	0,457	0,50	0.60	0,018	0'050	0.024
c2	0.457	0.50	0.60	0.018	0.020	0.024
D1	5.21			0.205		
E1	4.318			0.170		
θ1	0°	7°	15°	0°	7°	15°